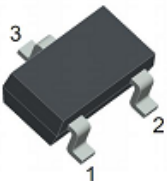
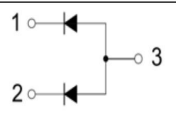
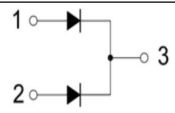
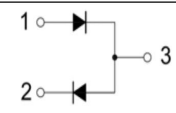


Switching Diodes		SOT-23 Plastic-Encapsulate Diodes	
<p><u>SOT-23</u></p> 		<p>Features</p> <ul style="list-style-type: none"> <li>• High Conductance</li> <li>• Fast Switching Speed</li> <li>• For General Purpose Switching Applications</li> </ul>	
BAW56	BAV70	BAV99	
			
MARKING:A1	MARKING:A4	MARKING:A7	

Solid dot = Green molding compound device, if none, the normal device.

**Maximum ratings (@Ta=25°C)**

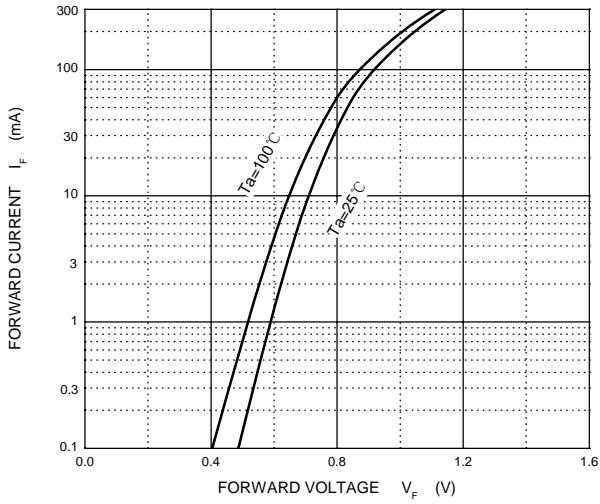
Parameter	Symbol	Limit	Unit
Reverse Voltage	VR	70	V
Forward Current	IF	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	IFSM	2.0	A
Power Dissipation	PD	225	mW
Thermal Resistance from Junction to Ambient	RθJA	556	°C/W
Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-55~+150	°C

**Electrical Characteristics (@Ta=25°C)**

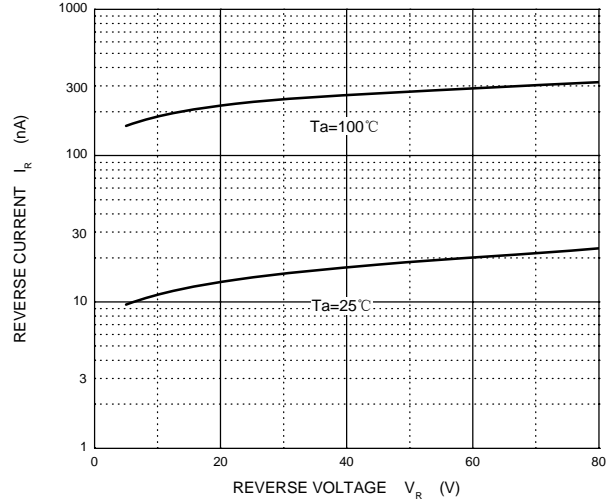
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse breakdown voltage	V(BR)	IR=100µA	70			V
Forward voltage	VF1	IF=1mA		0.57	0.715	V
	VF2	IF=10mA		0.714	0.855	V
	VF3	IF=50mA		0.83	1	V
	VF4	IF=150mA		0.97	1.25	V
Reverse current	IR	VR=70V			2.5	uA
capacitance Between terminals	Ctot	VR=0V,f=1MHz			1.5	PF
Reverse recovery time	t <sub>rr</sub>	IF=IR=10mA, I <sub>rr</sub> =0.1×IR,RL= 100 Ω			6	nS

**Typical Characteristics**

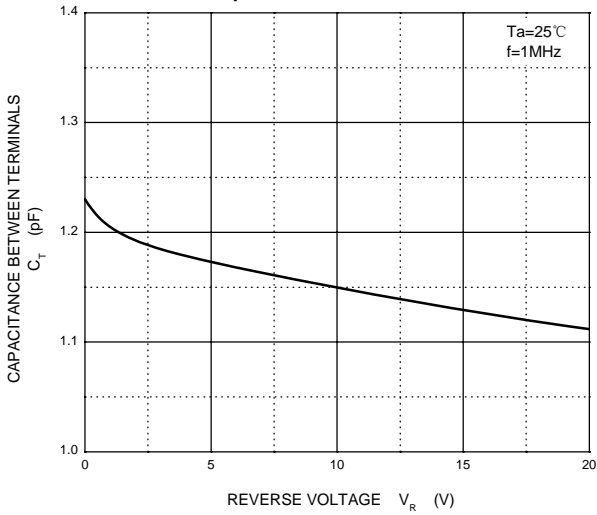
**Forward Characteristics**



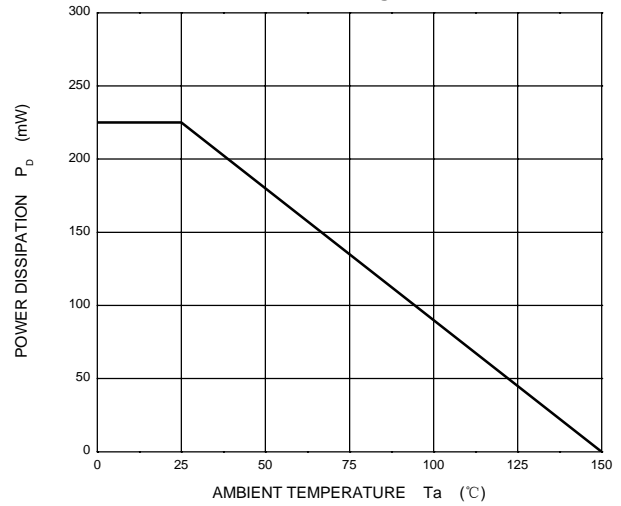
**Reverse Characteristics**



**Capacitance Characteristics**



**Power Derating Curve**



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)